



30NM60

Power MOSFET

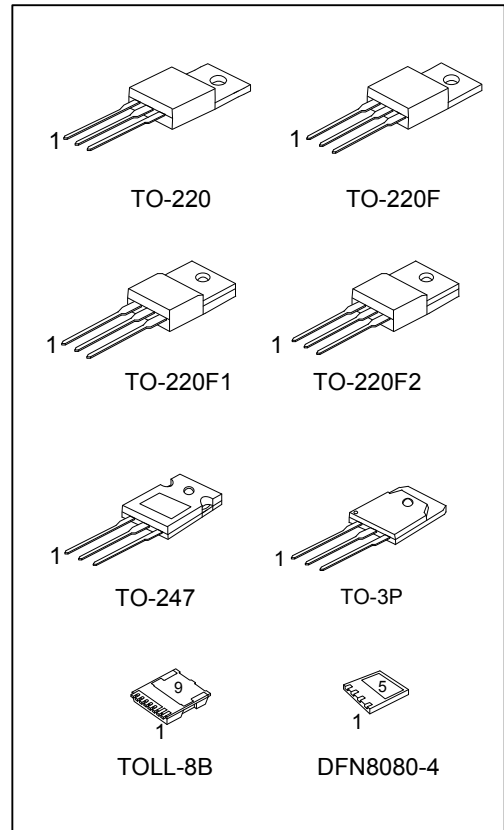
30A, 600V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

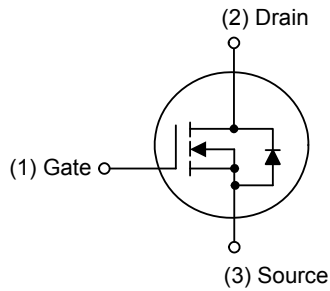
The **UTC 30NM60** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

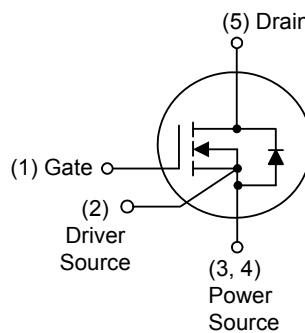
- * $R_{DS(ON)} \leq 0.13 \Omega @ V_{GS}=10V, I_D=15A$
- * High Switching Speed
- * 100% Avalanche Tested



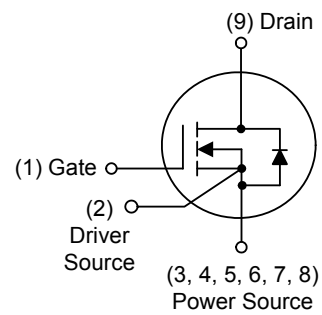
SYMBOL



TO-220 / TO-220F / TO-220F1
TO-220F2 / TO-247 / TO-3P



DFN8080-4



TOLL-8B

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment									Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	9	
30NM60L-TA3-T	30NM60G-TA3-T	TO-220	G	D	S	-	-	-	-	-	-	Tube
30NM60L-TF1-T	30NM60G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	-	Tube
30NM60L-TF2-T	30NM60G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	-	Tube
30NM60L-TF3-T	30NM60G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	-	Tube
30NM60L-T47-T	30NM60G-T47-T	TO-247	G	D	S	-	-	-	-	-	-	Tube
30NM60L-T3P-T	30NM60G-T3P-T	TO-3P	G	D	S	-	-	-	-	-	-	Tube
30NM60L-T8B-R	30NM60G-T8B-R	TOLL-8B	G	S	S	S	S	S	S	S	D	Tape Reel
30NM60L-K04-8080-R	30NM60G-K04-8080-R	DFN8080-4	G	S	S	S	S	'D	-	-	-	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>30NM60G-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, T47: TO-247, T3P: TO-3P</p> <p>T8B: TOLL-8B, K04-8080: DFN8080-4</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING

PACKAGE	MARKING
TO-220 / TO-220F TO-220F1 / TO-220F2 TO-247 / TO-3P	<p>UTC 30NM60</p> <p>Lot Code ← [][][][][] → Date Code</p> <p>L: Lead Free G: Halogen Free</p> <p>1</p>
DFN8080-4	<p>UTC 30NM60</p> <p>Lot Code ← [][][][][] → Date Code</p> <p>•</p>
TOLL-8B	<p>UTC 30NM60</p> <p>Lot Code ← [][][][][] → Date Code</p> <p>L: Lead Free G: Halogen Free</p> <p>1</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	30	A
	Pulsed (Note 2)	I_{DM}	60	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	1064	mJ
Peak Diode Recovery dv/dt		dv/dt	23	V/ns
MOSFET dv/dt Ruggedness		dv/dt	50	V/ns
Power Dissipation	TO-220	P_D	125	W
	TO-220F/TO-220F1 TO-220F2		40	W
	TO-247		150	W
	TO-3P		160	W
	TOLL-8B		220	W
	DFN8080-4		74	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 133\text{mH}$, $I_{AS} = 4.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-247/TO-3P TOLL-8B		40	$^\circ\text{C}/\text{W}$
	DFN8080-4		35 (Note)	$^\circ\text{C}/\text{W}$
	TO-220		0.97	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1 TO-220F2	θ_{JC}	3.125	$^\circ\text{C}/\text{W}$
	TO-247		0.83	$^\circ\text{C}/\text{W}$
	TO-3P		0.78	$^\circ\text{C}/\text{W}$
	TOLL-8B		0.56 (Note)	$^\circ\text{C}/\text{W}$
	DFN8080-4		1.68 (Note)	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

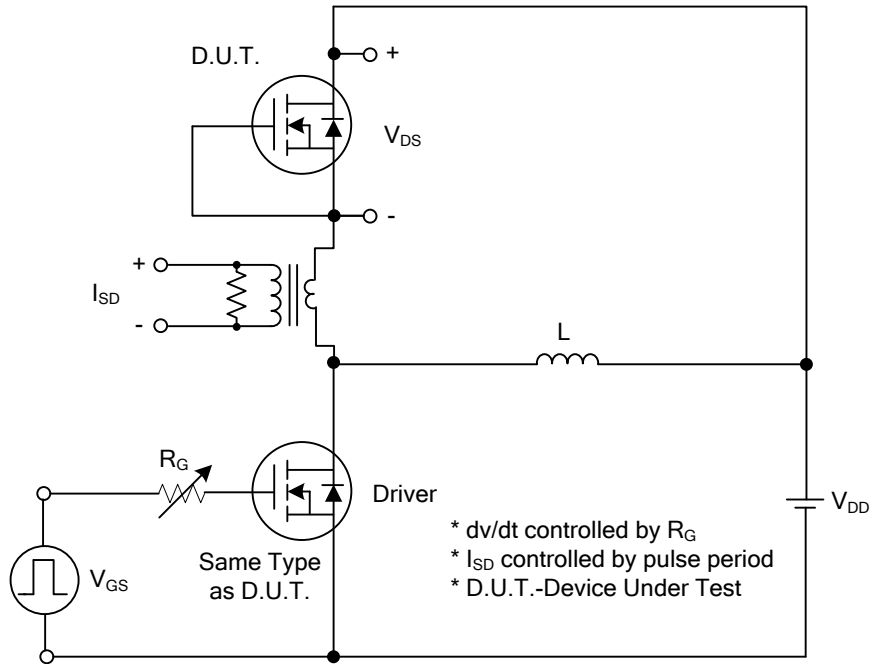
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
					Reverse	-100
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=15\text{A}$		0.105	0.13	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1.0\text{MHz}$		2423		pF
Output Capacitance	C_{OSS}			296		pF
Reverse Transfer Capacitance	C_{RSS}			26		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=480\text{V}$, $V_{GS}=10\text{V}$, $I_D=30\text{A}$ (Note 1, 2)		124		nC
Gate to Source Charge	Q_{GS}			34		nC
Gate to Drain Charge	Q_{GD}			46		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=100\text{V}$, $V_{GS}=10\text{V}$, $I_D=30\text{A}$, $R_G=25\Omega$ (Note 1, 2)		36		ns
Rise Time	t_R			34		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			270		ns
Fall-Time	t_F			100		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				30	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				60	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=30\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=15\text{A}$, $V_{GS}=0\text{V}$, $di_F/dt=100\text{A}/\mu\text{s}$ (Note 1)		465		ns
Body Diode Reverse Recovery Charge	Q_{rr}				8.7	

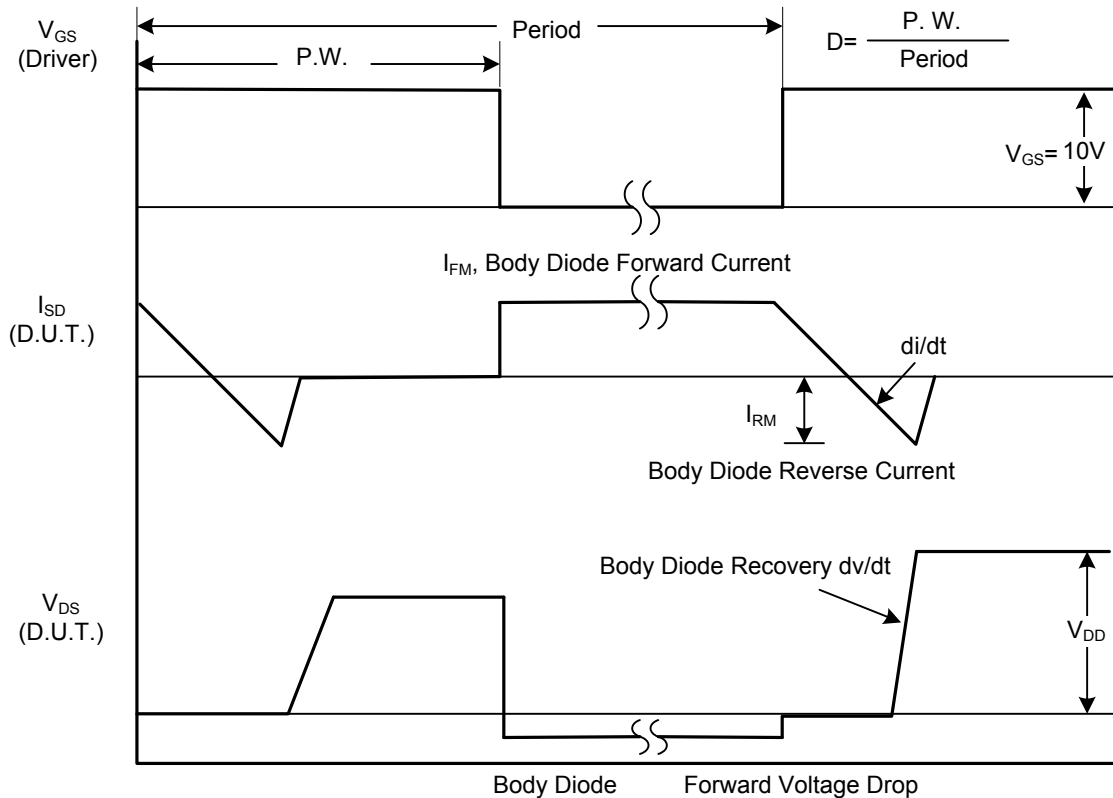
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS



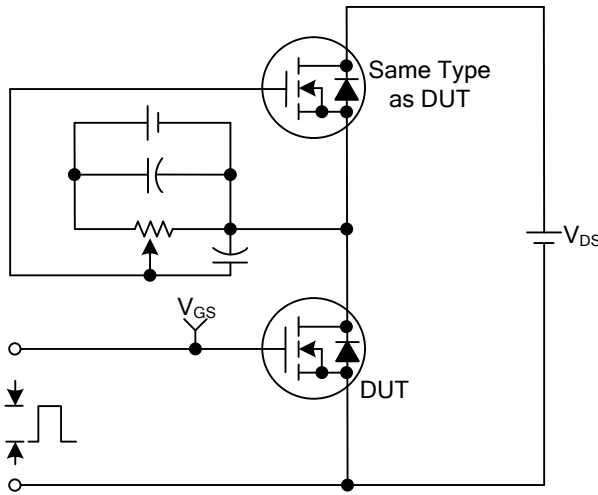
Peak Diode Recovery dv/dt Test Circuit



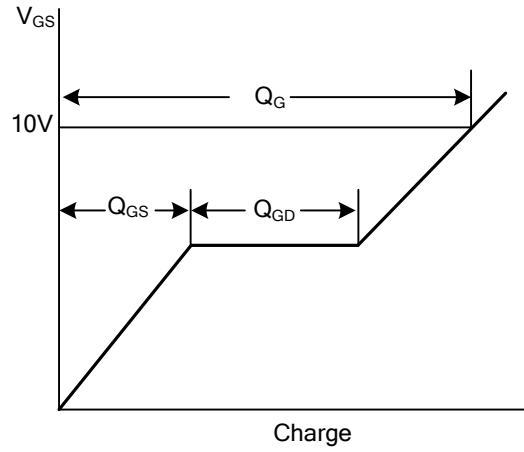
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS

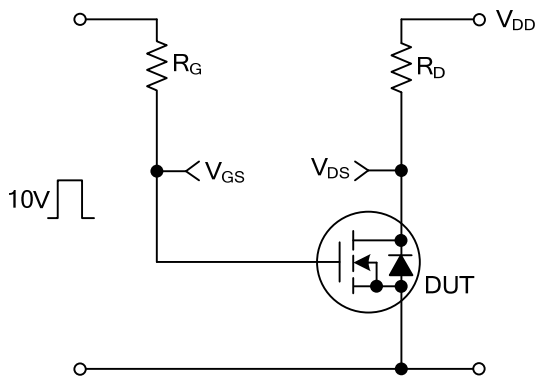
Gate Charge Test Circuit



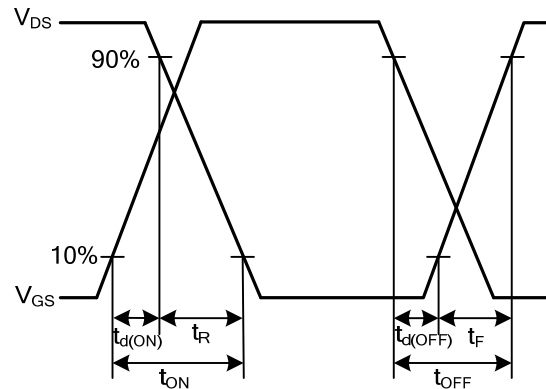
Gate Charge Waveforms



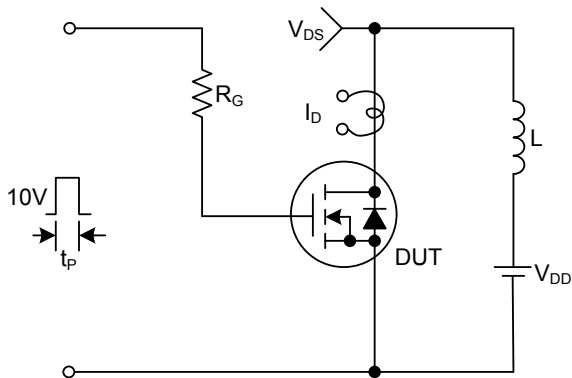
Resistive Switching Test Circuit



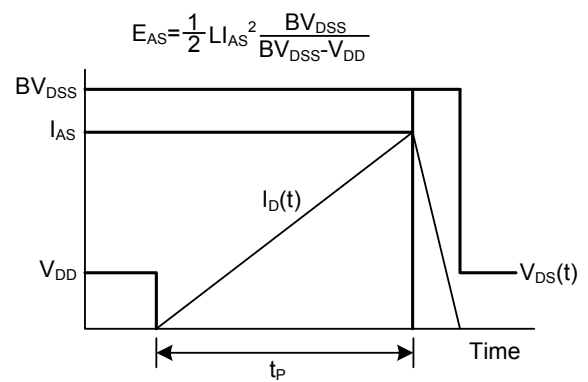
Resistive Switching Waveforms



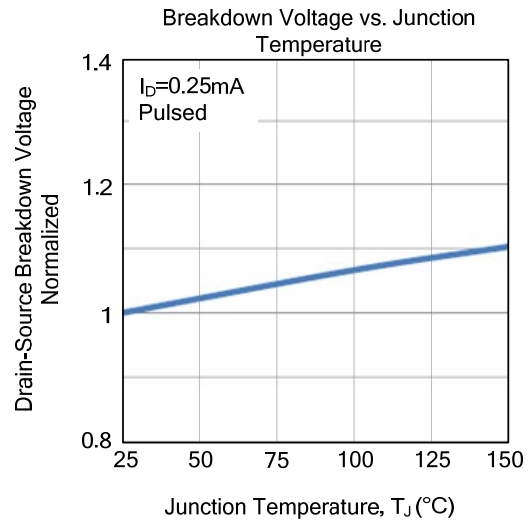
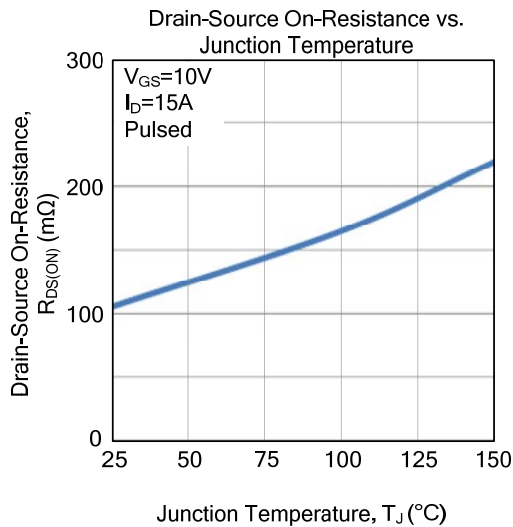
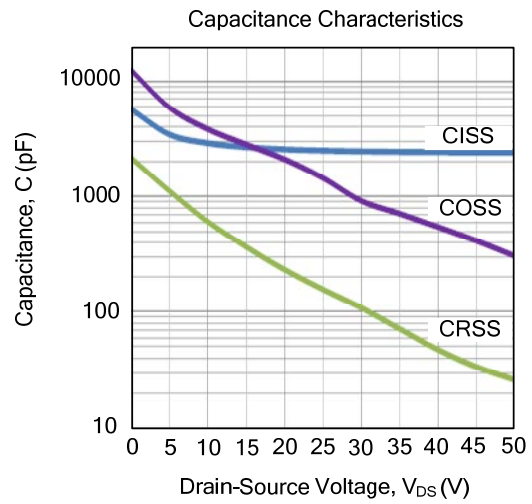
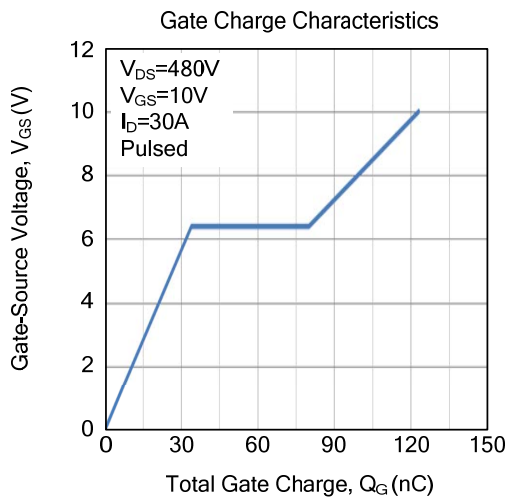
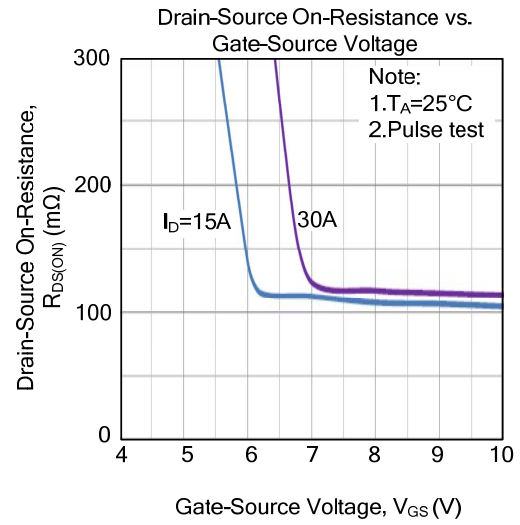
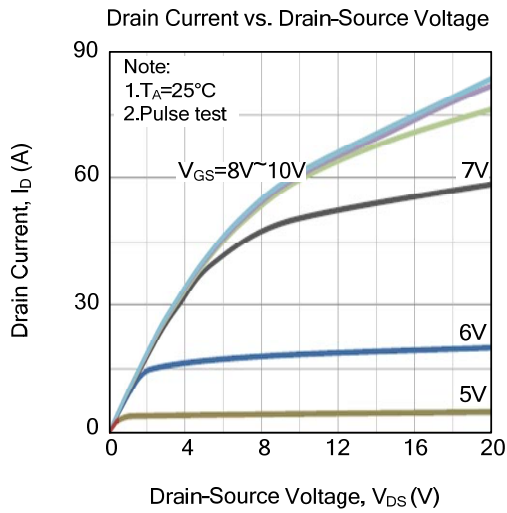
Unclamped Inductive Switching Test Circuit



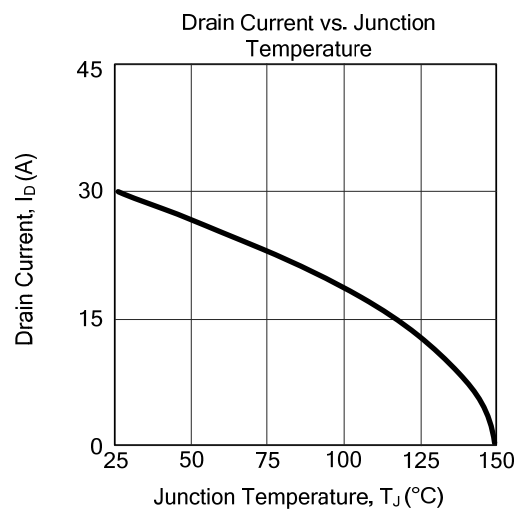
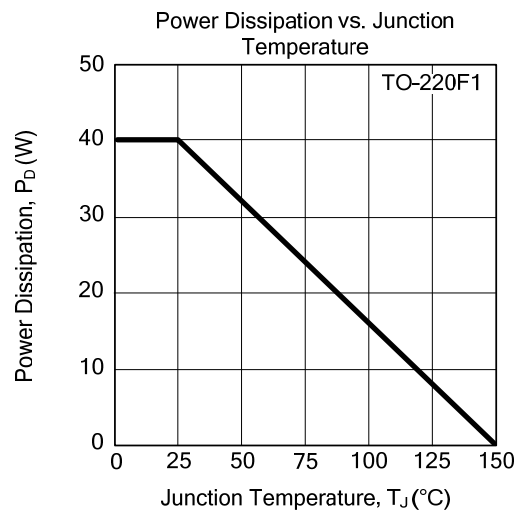
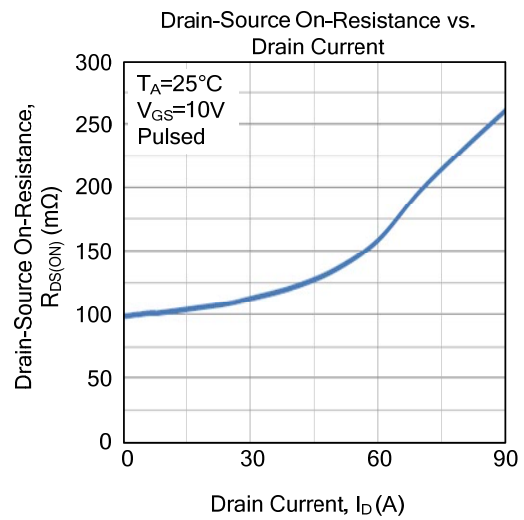
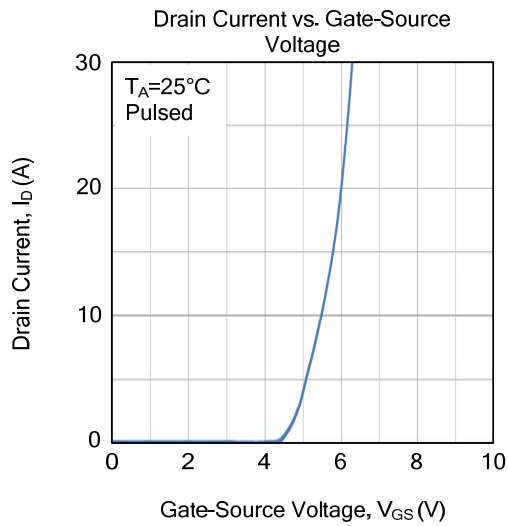
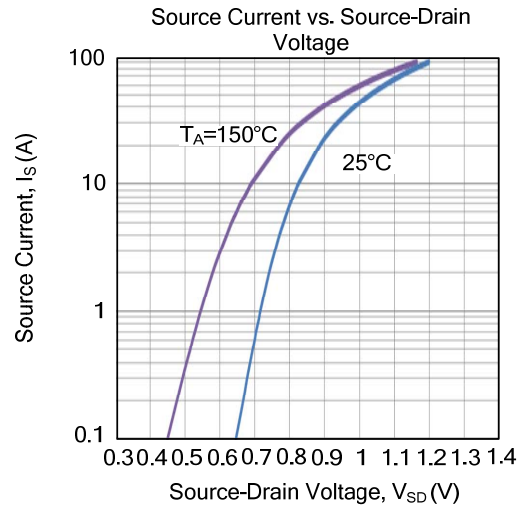
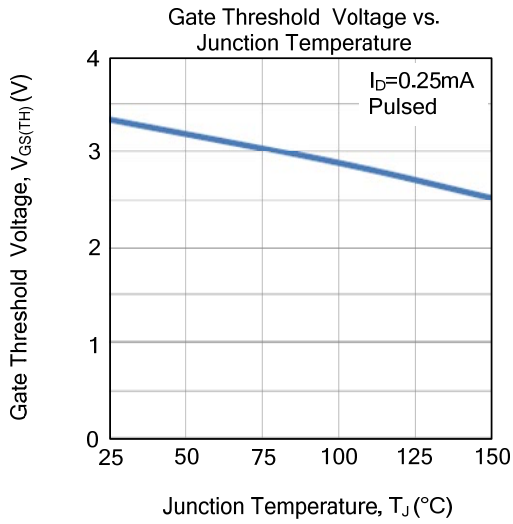
Unclamped Inductive Switching Waveforms



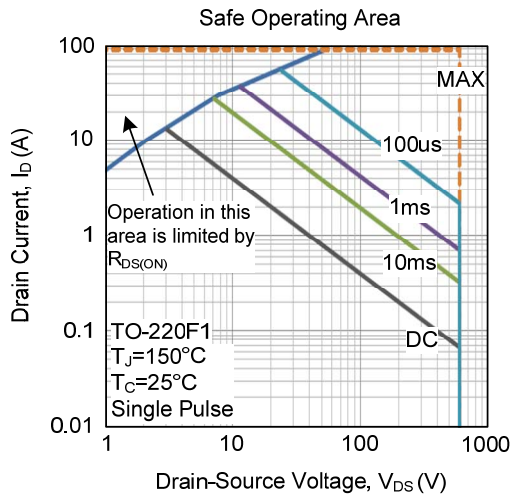
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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